David E Aspnes

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

213	15,683	60	123
papers	citations	h-index	g-index

219	16,569	3.4	6.26
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
213	Maximum-entropy revisited: Optimal filtering of spectra. *Journal of Applied Physics*, **2021**, 129, 224902	2.5	1
212	Critical Test of the Interaction of Surface Plasmon Resonances with Molecular Vibrational Transitions. *Journal of Physical Chemistry A*, **2020**, 124, 1744-1753	2.8	0
211	Quantitative assessment of linear noise-reduction filters for spectroscopy. *Optics Express*, **2020**, 28, 38917-38933	3.3	3
210	Classical Correlation Model of Resonance Raman Spectroscopy. *Journal of Physical Chemistry A*, **2020**, 124, 9177-9186	2.8	0
209	Extended Gaussian Filtering for Noise Reduction in Spectral Analysis. *Journal of the Korean Physical Society*, **2020**, 77, 819-823	0.6	4
208	Linear and nonlinear filtering of spectra. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2019**, 37, 051205	1.3	7
207	Dielectric Functions and Critical Points of GaAsSb Alloys. *Journal of the Korean Physical Society*, **2019**, 74, 595-599	0.6	3
206	Combined interpolation, scale change, and noise reduction in spectral analysis. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2019**, 37, 052903	1.3	11
205	Liquid gallium and the eutectic gallium indium (EGaIn) alloy: Dielectric functions from 1.24 to 3.1 eV by electrochemical reduction of surface oxides. *Applied Physics Letters*, **2016**, 109, 091905	3.4	33
204	Exciton-dominated Dielectric Function of Atomically Thin MoS2 Films. *Scientific Reports*, **2015**, 5, 16996	4.9	114
203	Bond models in linear and nonlinear optics **2015**,		2
202	Parameterization of the dielectric functions of InGaSb alloys. *Current Applied Physics*, **2014**, 14, 768-771	2.6	2
201	Interband transitions and dielectric functions of InGaSb alloys. *Applied Physics Letters*, **2013**, 102, 102109	3.4	5
200	Spectroscopic ellipsometry�A perspective. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2013**, 31, 058502	2.9	21
199	Shallow acceptor complexes in p-type ZnO. *Applied Physics Letters*, **2013**, 102, 152114	3.4	93
198	Plasmonics and Effective-Medium Theory **2013**, 203-224		1
197	Optical and structural characterization of epitaxial graphene on vicinal 6H-SiC(0001)�Si by spectroscopic ellipsometry, Auger spectroscopy, and STM. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 04E106	1.3	19

196	Control of the oxidation kinetics of H-terminated (111)Si by using the carrier concentration and the strain: a second-harmonic-generation investigation. *Journal of the Korean Physical Society*, **2012**, 60, 1685-1689	0.6	1
195	Bond-specific reaction kinetics during the oxidation of (111) Si: Effect of n-type doping. *Applied Physics Letters*, **2011**, 98, 021904	3.4	8
194	Effect of strain on bond-specific reaction kinetics during the oxidation of H-terminated (111) Si. *Applied Physics Letters*, **2011**, 98, 121912	3.4	8
193	Above-band-gap dielectric functions of ZnGeAs2: Ellipsometric measurements and quasiparticle self-consistent GW calculations. *Physical Review B*, **2011**, 83,	3.3	9
192	Back-reflection Second-harmonic Generation of (111)Si: Theory and Experiment. *Journal of the Korean Physical Society*, **2011**, 58, 1237-1243	0.6	3
191	Thickness inhomogeneities and growth mechanisms of GaP heteroepitaxy by organometallic chemical vapor deposition. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2010**, 28, 583-589	2.9	1
190	Dielectric functions and interband transitions of In1�AlxSb alloys. *Applied Physics Letters*, **2010**, 97, 111902	3.4	6
189	Chemical-etch-assisted growth of epitaxial zinc oxide. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2010**, 28, 689-692	2.9	
188	Ellipsometric study of single-crystal �InSe from 1.5 to 9.2 eV. *Applied Physics Letters*, **2010**, 96, 181902	3.4	13
187	Nondestructive analysis of coated periodic nanostructures from optical data. *Optics Letters*, **2010**, 35, 733-5	3	1
186	Measurement and control of in-plane surface chemistry during the oxidation of H-terminated (111) Si. *Proceedings of the National Academy of Sciences of the United States of America*, **2010**, 107, 17503-8	11.5	15
185	Bond models in linear and nonlinear optics. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1873-1880	1.3	5
184	Interband transitions of InAsxSb1� alloy films. *Applied Physics Letters*, **2009**, 95, 111902	3.4	23
183	Analytical solution of thickness variations in selective area growth by organometallic chemical vapor deposition. *Applied Physics Letters*, **2009**, 94, 253112	3.4	4
182	Plasmonic phenomena in indium tin oxide and ITO-Au hybrid films. *Optics Letters*, **2009**, 34, 2867-9	3	89
181	Follow the light: Ellipsometry and polarimetry. *Physics Today*, **2009**, 62, 70-71	0.9	3
180	Optical properties of InxAl1�As alloy films. *Applied Physics Letters*, **2008**, 92, 151907	3.4	13
179	Application of the anisotropic bond model to second-harmonic generation from amorphous media. *Physical Review B*, **2008**, 77,	3.3	22

178	Overlayer effects in the critical-point analysis of ellipsometric spectra: Application to InxGa1□As alloys. *Journal of Applied Physics*, **2008**, 103, 073502	2.5	4
177	Thickness inhomogenities in the organometallic chemical vapor deposition of GaP. *Applied Physics Letters*, **2008**, 93, 203104	3.4	4
176	Dependence of plasmon polaritons on the thickness of indium tin oxide thin films. *Journal of Applied Physics*, **2008**, 103, 093108	2.5	122
175	Model dielectric functions for AlxGa1□As alloys of arbitrary compositions. *Journal of Applied Physics*, **2008**, 104, 013515	2.5	13
174	Investigation of heteroepitaxy on nanoscopically roughened (001)Si by real-time spectroscopic polarimetry. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1312-1315		1
173	The anisotropic bond model of nonlinear optics. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 728-731	1.6	4
172	Dielectric properties of InAsP alloy thin films and evaluation of direct- and reciprocal-space methods of determining critical-point parameters. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 884-887	1.6	3
171	The nearly aligned rotating-monoplate compensator. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 739-742	1.6	2
170	Initial stages of GaP heteroepitaxy on nanoscopically roughened (001)Si. *Journal of Vacuum Science & Technology B*, **2007**, 25, 1448		6
169	Analytic determination of n, □and d of an absorbing film from polarimetric data in the thin-film limit. *Journal of Applied Physics*, **2007**, 101, 033109	2.5	14
168	Effect of overlayers on critical-point parameters in the analysis of ellipsometric spectra. *Applied Physics Letters*, **2007**, 91, 121903	3.4	15
167	Investigation of effective-medium approximation, alloy, average-composition, and graded-composition models for interface analysis by spectroscopic ellipsometry. *Journal of Applied Physics*, **2007**, 102, 063512	2.5	7
166	Dielectric functions and electronic structure of InAsxP1□ films on InP. *Applied Physics Letters*, **2007** , 91, 041917	3.4	15
165	Systematic approach for analyzing reflectance-difference spectra: Application to silicon-dielectric interfaces. *Applied Physics Letters*, **2006**, 88, 202112	3.4	7
164	Differences Between Charge Trapping States in Irradiated Nano-Crystalline HfO$_{2}$ and Non-Crystalline Hf Silicates. *IEEE Transactions on Nuclear Science*, **2006**, 53, 3644-3648	1.7	21
163	Toward n□ spectroscopy: Analytic solution of the three-phase model of polarimetry in the thin-film limit. *Applied Physics Letters*, **2006**, 88, 201107	3.4	4
162	Dielectric functions of AlxGa1□Sb (0.00?x?0.39) alloys from 1.5to6.0eV. *Journal of Applied Physics*, **2005**, 98, 104108	2.5	4
161	Real-time diagnostics for metalorganic vapor phase epitaxy. *Physica Status Solidi (B): Basic Research*, **2005**, 242, 2551-2560	1.3	5

160	Optical properties of (GaSb)3n(AlSb)n(1?n?5) superlattices. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2005**, 23, 1149		
159	Dipole-radiation model for terahertz radiation from semiconductors. *Applied Physics Letters*, **2005**, 86, 212109	3.4	1
158	Relative bulk and interface contributions to optical second-harmonic generation in silicon. *Physical Review B*, **2005**, 72,	3.3	14
157	Real-time characterization of GaSb homo- and heteroepitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2233		2
156	Spectroscopic ellipsometric analysis of interfaces: Comparison of alloy and effective-medium-approximation approaches to a CdMgTe multilayer system. *Applied Physics Letters*, **2004**, 85, 946-948	3.4	4
155	Calculation of bulk third-harmonic generation from crystalline Si with the simplified bond hyperpolarizability model. *Physical Review B*, **2004**, 70,	3.3	13
154	Optical properties of Cd1�MgxTe (x=0.00, 0.23, 0.31, and 0.43) alloy films. *Applied Physics Letters*, **2004**, 84, 693-695	3.4	11
153	Optimizing precision of rotating-analyzer and rotating-compensator ellipsometers. *Journal of the Optical Society of America A: Optics and Image Science, and Vision*, **2004**, 21, 403-10	1.8	30
152	Application of the simplified bond-hyperpolarizability model to fourth-harmonic generation. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2003**, 21, 1798		8
151	Simplified bond-hyperpolarizability model of second- and fourth-harmonic generation: application to Si�SiO2 interfaces. *Physica Status Solidi (B): Basic Research*, **2003**, 240, 509-517	1.3	2
150	Dielectric functions of InxGa1�As alloys. *Physical Review B*, **2003**, 68,	3.3	39
149	Pseudodielectric function of ZnGeP2 from 1.5 to 6 eV. *Applied Physics Letters*, **2002**, 81, 628-630	3.4	3
148	Simplified bond-hyperpolarizability model of second harmonic generation. *Physical Review B*, **2002**, 65,	3.3	59
147	Simplified bond-hyperpolarizability model of second harmonic generation: Application to Si-dielectric interfaces. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1699		17
146	Pseudodielectric functions of InGaAs alloy films grown on InP. *Applied Physics Letters*, **2002**, 81, 2367-2369	3.4	9
145	Elimination of endpoint-discontinuity artifacts in the analysis of spectra in reciprocal space. *Journal of Applied Physics*, **2001**, 89, 8183-8192	2.5	21
144	Ordinary and extraordinary dielectric functions of 4H�and 6H�SiC from 3.5 to 9.0 eV. *Applied Physics Letters*, **2001**, 78, 2715-2717	3.4	21
143	Investigation of noise in a spectrometer system using a short-arc source. *Review of Scientific Instruments*, **2001**, 72, 3477-3479	1.7	4

142	Nondestructive Measurement of a Glass Transition Temperature at Spin-Cast Semicrystalline Polymer Surfaces. *Macromolecules*, **2001**, 34, 2395-2397	5.5	17
141	Determination and Critical Assessment of the Optical Properties of Common Substrate Materials Used in III-V Nitride Heterostructures with Vacuum Ultraviolet Spectroscopic Ellipsometry. *Materials Research Society Symposia Proceedings*, **2001**, 693, 745		1
140	Ordinary and Extra-Ordinary Dielectric Function of 4h- and 6H-SiC in the 0.7 to 9.0 eV Photon Energy Range. *Materials Research Society Symposia Proceedings*, **2000**, 640, 1		0
139	Effect of Ar+ ion beam in the process of plasma surface modification of PET films. *Journal of Applied Polymer Science*, **2000**, 77, 1679-1683	2.9	15
138	Real-time optical techniques and QMS to characterize growth in a modified commercial OMVPE reactor. *Journal of Electronic Materials*, **2000**, 29, 106-111	1.9	4
137	Surface-induced optical anisotropy of Si and Ge. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2000**, 18, 2229		11
136	Isotopic effects on the dielectric response of Si around the E1 gap. *Physical Review B*, **2000**, 61, 12946-12951	3.3	29
135	Visible-near ultraviolet ellipsometric study of Zn1□MgxSe and Zn1□BexSe alloys. *Journal of Applied Physics*, **2000**, 88, 878-882	2.5	19
134	Real-time optical characterization of heteroepitaxy by organometallic chemical vapor deposition. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2000**, 18, 1184-1189	2.9	15
133	Optical properties of AlxGa1□P (0?x?0.52) alloys. *Journal of Applied Physics*, **2000**, 87, 1287-1290	2.5	25
132	Dielectric function of epitaxial ZnSe films. *Applied Physics Letters*, **2000**, 77, 3364-3366	3.4	11
131	Combined beam profile reflectometry, beam profile ellipsometry and ultraviolet-visible spectrophotometry for the characterization of ultrathin oxide-nitride-oxide films on silicon. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1999**, 17, 380-384	2.9	12
130	Comment on □Ab Initio Calculation of Excitonic Effects in the Optical Spectra of Semiconductors□ *Physical Review Letters*, **1999**, 83, 3970-3970	7.4	23
129	Analysis of high-index Si(001) surfaces by reflectance difference spectroscopy. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1999**, 17, 1652-1656	2.9	4
128	High-Resolution Spectroscopy with Reciprocal-Space Analysis. *Physica Status Solidi (B): Basic Research*, **1999**, 215, 715-723	1.3	7
127	Photon-induced localization and final-state correlation effects in optically absorbing materials. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 2367		13
126	Reflectance difference spectroscopy spectra of clean (3□), (2□), and c(2□) 3C-SiC(001) surfaces: New evidence for surface state contributions to optical anisotropy spectra. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 2355		15
125	Analytic representations of the dielectric functions of crystalline and amorphous Si and crystalline Ge for very large scale integrated device and structural modeling. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1998**, 16, 1654-1657	2.9	19

No.	Publication	IF	Citations
124	Trends in residual stress for GaN/AlN/6H�SiC heterostructures. *Applied Physics Letters*, **1998**, 73, 2808-2810	3.4	40
123	Relaxation Phenomena in GaN/AlN/6H�SiC Heterostructures. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		
122	Evidence of near-surface localization of excited electronic states in crystalline Si. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1997**, 15, 1196		23
121	Surface and interface effects on ellipsometric spectra of crystalline Si. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1997**, 15, 1205		23
120	Ellipsometric studies of Cd1�MgxTe (0?x?0.5) alloys. *Applied Physics Letters*, **1997**, 71, 249-251	3.4	22
119	Low pH Chemical Etch Route for Smooth H-Terminated Si(100) and Study of Subsequent Chemical Stability. *Materials Research Society Symposia Proceedings*, **1997**, 477, 191		
118	Spectroscopic ellipsometric characterization of undoped ZnTe films grown on GaAs. *Applied Physics Letters*, **1997**, 70, 610-612	3.4	33
117	Variation of GaN valence bands with biaxial stress and quantification of residual stress. *Applied Physics Letters*, **1997**, 70, 2001-2003	3.4	45
116	Optical investigations of surface processes in GaP heteroepitaxy on silicon under pulsed chemical beam epitaxy conditions. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 3040		8
115	New approach to preparing smooth Si(100) surfaces: Characterization by spectroellipsometry and validation of Si/SiO2 interfaces properties in metal-oxide-semiconductor devices. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 2812		6
114	Real-time assessment of overlayer removal on GaN, AlN, and AlGaN surfaces using spectroscopic ellipsometry. *Applied Physics Letters*, **1996**, 69, 2065-2067	3.4	55
113	Real-time optical diagnostics for epitaxial growth **1996**,		2
112	Growth, Doping and Characterization of AlxGa1-xN Thin Film Alloys on 6H-SiC(0001) Substrates. *MRS Internet Journal of Nitride Semiconductor Research*, **1996**, 1, 1		94
111	Multilevel Approaches Toward Monitoring and Control of Semiconductor Epitaxy. *Materials Research Society Symposia Proceedings*, **1996**, 448, 451		1
110	Variation of GaN Valence Bands with Biaxial Stress: Quantification of Residual Stress and Impact on Fundamental Band Parameters. *Materials Research Society Symposia Proceedings*, **1996**, 449, 781		2
109	In-Plane Optical Anisotropies of AlxGa1�N Films in Their Regions of Transparency. *Materials Research Society Symposia Proceedings*, **1996**, 449, 835		2
108	Optical approaches to determine near-surface compositions during epitaxy. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1996**, 14, 960-966	2.9	36
107	Reciprocal-space analysis of photoluminescence and photoluminescence excitation spectra. *Applied Physics Letters*, **1996**, 68, 3230-3232	3.4	4

106	Investigation of the relationship between reflectance difference spectroscopy and surface structure using grazing incidence X-ray scattering. *Physica Status Solidi A*, **1995**, 152, 9-21		32
105	Real-time observation of atomic ordering in (001) In0.53Ga0.47As epitaxial layers. *Physical Review Letters*, **1995**, 74, 3640-3643	7.4	37
104	Performance capabilities of reflectometers and ellipsometers for compositional analysis during AlxGa1�As epitaxy. *Applied Physics Letters*, **1995**, 66, 1617-1619	3.4	7
103	Surface-Induced Optical Anisotropies of Single-Domain (2 x 1) Reconstructed (001) Si and Ge Surfaces. *Physical Review Letters*, **1995**, 74, 3431-3434	7.4	108
102	Analysis of Strain in GaN on Al2O3 and 6H-SiC: Near-Bandedge Phenomena. *Materials Research Society Symposia Proceedings*, **1995**, 395, 405		7
101	Real-time Optical Monitoring of GaxIn1�P/GaP Heterostructures on Silicon. *Materials Research Society Symposia Proceedings*, **1995**, 406, 127		
100	In-Situ and Ex-Situ Studies of Silicon Interfaces and Nanostructures by Ellipsometry and RDS. *Materials Research Society Symposia Proceedings*, **1995**, 406, 371		1
99	As capture and the growth of ultrathin InAs layers on InP. *Applied Physics Letters*, **1994**, 64, 3279-3281	3.4	13
98	As capture and the growth of ultrathin InAs layers on InP. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1994**, 12, 1180-1185	2.9	9
97	Study of strain and disorder of InxGa1�P/(GaAs, graded GaP) (0.25��0.8) using spectroscopic ellipsometry and Raman spectroscopy. *Journal of Applied Physics*, **1994**, 75, 5040-5051	2.5	51
96	Optical-standard surfaces of single-crystal silicon for calibrating ellipsometers and reflectometers. *Applied Optics*, **1994**, 33, 7435-8	1.7	71
95	Optical anisotropy of singular and vicinal Si�SiO2 interfaces and H-terminated Si surfaces. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1994**, 12, 1152-1157	2.9	72
94	Optical study of (AlxGa1�)0.5In0.5P/GaAs semiconductor alloys by spectroscopic ellipsometry. *Journal of Applied Physics*, **1993**, 73, 400-406	2.5	24
93	Minimal-data approaches for determining outer-layer dielectric responses of films from kinetic reflectometric and ellipsometric measurements. *Applied Physics Letters*, **1993**, 62, 343-345	3.4	23
92	Real-Time Surface and Near-Surface Optical Diagnostics for Epitaxial Growth. *Materials Research Society Symposia Proceedings*, **1993**, 324, 3		4
91	Minimal-data approaches for determining outer-layer dielectric responses of films from kinetic reflectometric and ellipsometric measurements. *Journal of the Optical Society of America A: Optics and Image Science, and Vision*, **1993**, 10, 974	1.8	111
90	Optical dielectric response of PdO. *Physical Review B*, **1992**, 46, 15085-15091	3.3	13
89	Growth of AlxGa1�As parabolic quantum wells by real-time feedback control of composition. *Applied Physics Letters*, **1992**, 60, 1244-1246	3.4	97

88	Formation of The Interface between InP and Arsenic Based Alloys by Chemical Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1992**, 263, 267		5
87	Surface science at atmospheric pressure: Reconstructions on (001) GaAs in organometallic chemical vapor deposition. *Physical Review Letters*, **1992**, 68, 627-630	7.4	201
86	Reflectance-difference spectroscopy of (001) GaAs surfaces in ultrahigh vacuum. *Physical Review B*, **1992**, 46, 15894-15904	3.3	305
85	Real-time optical diagnostics for epitaxial growth. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1991**, 9, 870-875	2.9	14
84	In situ determination of free-carrier concentrations by reflectance difference spectroscopy. *Applied Physics Letters*, **1991**, 59, 3443-3445	3.4	79
83	Optical control of growth of AlxGa1�As by organometallic molecular beam epitaxy. *Applied Physics Letters*, **1990**, 57, 2707-2709	3.4	63
82	Application of ellipsometry to crystal growth by organometallic molecular beam epitaxy. *Applied Physics Letters*, **1990**, 56, 2569-2571	3.4	99
81	Direct optical measurement of surface dielectric responses: Interrupted growth on (001) GaAs. *Physical Review Letters*, **1990**, 64, 192-195	7.4	100
80	Low-retardance fused-quartz window for real-time optical applications in ultrahigh vacuum. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1989**, 7, 3291-3294	2.9	71
79	Optical properties of copper-oxygen planes in superconducting oxides and related materials. *Physical Review B*, **1989**, 40, 6797-6805	3.3	96
78	Kinetic limits of monolayer growth on (001) GaAs by organometallic chemical-vapor deposition. *Physical Review Letters*, **1988**, 61, 2782-2785	7.4	129
77	Oxygen-deficiency-induced localized optical excitations in YBa2Cu. *Physical Review B*, **1988**, 38, 870-873	3.3	96
76	Optical anisotropy of YBa2Cu3O7-x. *Physical Review B*, **1988**, 38, 5077-5080	3.3	69
75	Application of reflectance difference spectroscopy to molecular-beam epitaxy growth of GaAs and AlAs. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1988**, 6, 1327-1332	2.9	473
74	Correlation of dopant-induced optical transitions with superconductivity in La2-xSrxCuO4- delta. *Physical Review B*, **1988**, 37, 3396-3399	3.3	71
73	Semiconductor topography in aqueous environments: Tunneling microscopy of chemomechanically polished (001) GaAs. *Applied Physics Letters*, **1987**, 50, 1742-1744	3.4	51
72	Substantially Transparent Pt, Pd, Rh, And Re Films: Preparation and Properties. *Materials Research Society Symposia Proceedings*, **1987**, 111, 379		2
71	Optical Reflectance and Rheed Transients During Mbe Growth on (001) GaAs. *Materials Research Society Symposia Proceedings*, **1987**, 91, 57		6

70	Optical reflectance and electron diffraction studies of molecular-beam-epitaxy growth transients on GaAs(001). *Physical Review Letters*, **1987**, 59, 1687-1690	7.4	193
69	Microstructurally engineered, optically transmissive, electrically conductive metal films. *Journal of Applied Physics*, **1986**, 60, 3028-3034	2.5	32
68	Grain-size effects in the parallel-band absorption spectrum of aluminum. *Physical Review B*, **1986**, 33, 5363-5367	3.3	18
67	Multiple determination of the optical constants of thin-film coating materials: a Rh sequel. *Applied Optics*, **1986**, 25, 1299	1.7	15
66	Optical properties of AlxGa1� As. *Journal of Applied Physics*, **1986**, 60, 754-767	2.5	723
65	Experiment and theory of �transparent� metal films. *Nature*, **1985**, 313, 664-666	50.4	23
64	Anisotropies in the above-bandgap optical spectra of cubic semiconductors. *Physical Review Letters*, **1985**, 54, 1956-1959	7.4	366
63	Structural and Microstructural Determinations of Crystalline and Amorphous Fractions of Microcrystalline Ge: A Comparison **1985**, 841-844		1
62	Nondestructive analysis of Hg1�CdxTe (x=0.00, 0.20, 0.29, and 1.00) by spectroscopic ellipsometry. I. Chemical oxidation and etching. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1984**, 2, 1309-1315	2.9	83
61	Spectroscopic ellipsometric and He backscattering analyses of crystalline Si-SiO2 mixtures grown by molecular beam epitaxy. *Applied Physics Letters*, **1984**, 44, 517-519	3.4	11
60	Nondestructive analysis of Hg1�CdxTe (x=0.00, 0.20, 0.29, and 1.00) by spectroscopic ellipsometry. II. Substrate, oxide, and interface properties. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1984**, 2, 1316-1323	2.9	95
59	Fourier Analysis Of Optical Spectra: Application To AlxGa1-xAs And GaAs1-xPx **1984**, 0452, 79		2
58	Dielectric properties of heavily doped crystalline and amorphous silicon from 1.5 to 6.0 eV. *Physical Review B*, **1984**, 29, 768-779	3.3	294
57	Optical properties and damage analysis of GaAs single crystals partly amorphized by ion implantation. *Journal of Applied Physics*, **1984**, 56, 2664-2671	2.5	186
56	Properties of Hg0.71Cd0.29Te and some native oxides by spectroscopic ellipsometry. *Journal of Applied Physics*, **1983**, 54, 7132-7138	2.5	37
55	Analysis of optical spectra by Fourier methods: filtering and least-squares regression in reciprocal space. *Journal of the Optical Society of America*, **1983**, 73, 1759		16
54	Dielectric functions and optical parameters of Si, Ge, GaP, GaAs, GaSb, InP, InAs, and InSb from 1.5 to 6.0 eV. *Physical Review B*, **1983**, 27, 985-1009	3.3	3051
53	ELLIPSOMETRIC STUDIES OF GaAs1-xPx : FOURIER ANALYSIS OF CRITICAL POINT COMPLEXES. *Journal De Physique Colloque*, **1983**, 44, C10-45-C10-48		2

52	Summary Abstract: Preparation of high-quality surfaces on semiconductors by selective chemical etching. *Journal of Vacuum Science and Technology*, **1982**, 20, 488-489		16
51	Optical properties of In1�GaxAsyP1� from 1.5 to 6.0 eV determined by spectroscopic ellipsometry. *Physical Review B*, **1982**, 26, 6669-6681	3.3	96
50	Direct Determination of Sizes of Excitations from Optical Measurements on Ion-Implanted GaAs. *Physical Review Letters*, **1982**, 48, 1863-1866	7.4	78
49	Local-field effects and effective-medium theory: A microscopic perspective. *American Journal of Physics*, **1982**, 50, 704-709	0.7	541
48	Optical Properties of GaAs and Its Electrochemically Grown Anodic Oxide from 1.5 to 6.0 eV. *Journal of the Electrochemical Society*, **1981**, 128, 590-597	3.9	108
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